Blue and red light photoluminescence emission at room temperature from CaTiO$_3$ decorated with $\alpha$-Ag$_2$WO$_4$

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**ABSTRACT**

CaTiO$_3$ (CT) and $\alpha$-Ag$_2$WO$_4$ (AW) semiconductors are widely known for their interesting electrical and photoluminescence (PL) properties. In this study, we decorated CT with AW for obtaining CaTiO$_3$:AW (CT:AW), and investigated the properties of the produced materials, especially their PL properties. The X-ray diffraction peaks of the synthesized microcrystals were well indexed to the orthorhombic phase for all the samples. Two morphologies: cube-like for CT and rod-like for AW were observed by field-emission scanning electron microscopy (FE-SEM). The FE-SEM and transmission electron microscopy (TEM) studies indicated the presence of rod-shaped AW deposited on the surfaces of cube-shaped CT morphology. PL emission of the decorated samples overlaps all the visible region spectra because of the contribution from both the constituent materials that induce maximum emissions in the blue and red regions. The examination of Commission internationale de l’éclairage (CIE) coordinates confirmed that the decorated samples exhibit favored emission in the red wavelength region.

1. Introduction

Technological applications of semiconductor materials have stimulated the research for improving or modulating their properties [1–3]. Recently, semiconductors exhibiting photoluminescence (PL) properties have received significant attention owing to their applications in several devices such as light emitting diodes (LEDs), displays, and optical markers [4]. Among the various semiconductor materials exhibiting PL properties, CaTiO$_3$ (CT) and $\alpha$-Ag$_2$WO$_4$ (AW) have received a special attention [5–8].

CT is a perovskite material that exhibits PL properties in both semi-ordered and amorphous forms [9–11]. CT is present in four structurally stable forms: cubic, monoclinic, tetragonal, and orthorhombic phases [12]. Orthorhombic CT exhibits PL at room temperature, which is associated with the structural organization of the material. This organization depends on the method of synthesis, time, and heat treatment temperature (if any) of the material since these parameters influence its structural organization [13,14]. PL properties of CT can be attributed to the lattice defects such as oxygen vacancies. These defects modify the coordination of titanium and calcium atoms, thereby affecting the PL properties [15–17].

Moreira et al. [18] synthesized CT using a microwave-assisted hydrothermal (MAH) method by varying the synthesis time from 10 to 160 min. PL properties of the obtained powders were examined at room temperature using an excitation wavelength of 350.7 nm. A broadband profile was observed that was attributed to the presence of intermediate energy states within the band gap; the intrinsic defects present in the material were responsible for the energy states.

The semiconductor material, AW, exists in three structural forms, $\alpha$-orthorhombic, $\beta$-hexagonal, and $\gamma$-cubic phases, depending on the reaction conditions (temperature and pH) employed in the synthesis [19]. The properties of AW are known to depend on the interactions between the octahedral clusters of [WO$_6$] and [AgO$_x$] ($x=2, 4, 6, \text{and} 7$) [20]. Lin et al. [21] examined the PL properties of AW and concluded that the PL emissions could be attributed to the charge transfer occurring from the distorted [WO$_6$] clusters to the undistorted [WO$_6$] clusters.

Considering the interesting PL proprieties of CT and AW semiconductors, we aimed at combining both the materials in order to prepare an advanced material that can exhibit features resulting from the formation of the decorated. AW was synthesized using a coprecipitation (CP) method with a mixture of saturated solutions of the soluble precursor reagent. This low-cost method is simple and uses a low reaction temperature, good homogeneity and uniform-sized particles [22]. CT was synthesized by the MAH method, a high-energy
2.3. Synthesis of CaTiO₃

The CT microparticles were prepared by modifying a method reported by Mazzo et al. [25]. Initially, calcium chloride, 0.01 mol of CaCl₂·2H₂O (99.0%, Sigma-Aldrich) was dissolved in 50 mL distilled water in a Teflon autoclave under stirring with a continuous flow of N₂. After 5 min, 0.01 mol of titanium isopropoxide, Ti(OC₃H₇)₄ (97%, Sigma-Aldrich) was added in solution and stirred for 20 min 50 mL KOH (6 M) solution was then added to this solution in order to act as the mineralizer. The precipitate formed was then processed by the MAH method, by heating at 140 °C for different times (4, 8, 16, and 32 min) at 140 °C by the MAH method. All the diffraction peaks could be indexed to the orthorhombic phase with a space group of Pbnm according to the Joint Committee on Powder Diffraction Standards (JCPDS) card No. 42-0423 [27]. The 4, 8, and 16 min samples exhibit a halo in the baseline, located between 20° and 40°, indicating the presence of an amorphous phase in the samples. However, with an increase in the synthesis time, the crystallinity of the samples improved, resulting in a decrease in this halo. Hence, CT exhibits a long-range disorganization, which decreases with an increase in the synthesis time.

In order to confirm the short-range organization of the material, Raman measurements were carried out, and the results are presented in Fig. 1(b). The observed Raman-active vibration modes correspond to the Ca-TiO₃ lattice mode. The peaks located at 178, 221, 243, 285, and 339 cm⁻¹ are assigned to the O-Ti-O bending modes. The peaks detected at 461 and 540 cm⁻¹ are attributed to the torsional vibration in TiO₃, and the peak at 685 cm⁻¹ is assigned to the Ti-O symmetric stretching vibration [29,30]. A broadband is observed in the range of 600–750 cm⁻¹ in the Raman spectra of all the CT samples. However, in the case of the CT sample obtained with a synthesis time of 4 min, two small peaks (two horizontal arrows) are observed in the 600–750 cm⁻¹ range, suggesting the presence of two titanium clusters [TiO₆] and [TiO₅] in the sample [14].

Thus, some of the Raman peaks are not well defined in the case of the 4 and 8 min CT samples, indicating the short-range structural disorder present in the samples. The Raman spectra obtained for the 16 and 32 min CT samples exhibit more well-defined peaks, indicating a possible decrease in the defects and an increase in the crystallinity of the sample [31]. Moreover, all the CT samples exhibit a peak in the 800–900 cm⁻¹ range, suggesting a cation order-disorder, which is more evident in the 4 and 8 min CT samples [32]. Thus, all the CT samples treated for different times at 140 °C using the MAH method exhibit a low short-range organization due to a degree of the structural order-disorder.

The morphology of the CT samples reflects their structural organization and (the FE-SEM images are shown in Fig. 1(c). The CT sample prepared using a synthesis time of 4 min by the MAH method consists of micro-cubes with edge lengths in the order of 3.3 ± 0.1 μm. It can be seen amorphous parts in the sample which is formed by aggregate of particles that were nucleation process and self-assembly. With a synthesis time of 8 min, a sample consisting of micro-cubes with edge lengths in the order of 4.3 ± 0.1 μm, it can be seen amorphous parts in the sample which is formed by aggregate of particles that were nucleation process and self-assembly. With a synthesis time of 8 min, a sample consisting of micro-cubes with edge lengths in the order of 4.3 ± 0.1 μm, it can be seen amorphous parts in the sample which is formed by aggregate of particles that were nucleation process and self-assembly.
synthesized with 16 min consists of edges with lengths in the order of 5.0 ± 0.8 µm. For the 32 min CT sample presents lengths of 5 ± 1 µm, a variation in the size is not observed. Thus, the growth and organization of particles enhanced with an increase in the synthesis time, as observed with the XRD and Raman examinations.

For the AW sample obtained by the CP method, intense and well-defined peaks are observed in the XRD pattern, indicating their crystallinity and long-range structural order (Fig. 1(d)). The peaks can be indexed to the orthorhombic phase with a space group of $Pn2_1$ and a point-group of symmetry of $C_{2h}^{10}$, in agreement with the JCPDS card No. 34–61 [33].

The Raman spectrum of the AW sample exhibits 13 active modes, which could be assigned to the point-group symmetry of $C_{2h}^{10}$ (Fig. 1(e)). The band observed at 881 cm$^{-1}$ corresponds to the symmetric stretching mode of $[WO_6]$ clusters. The peaks observed between 500 and 50 cm$^{-1}$ can be assigned to the external vibrational modes of $[AgO_x]$ ($x=7, 6, 4, \text{ and } 2$) clusters [8, 34, 35]. The modes are not well defined, indicating the short-range structural disorder present in the sample.

The morphology and the microstructure of the AW sample were investigated by examining their FE-SEM images. The FE-SEM image of the AW crystals indicates the presence of uniform rod-like morphology with a diameter of 0.14 ± 0.2 µm (Fig. 1(f)).

The XRD patterns of the decorated samples are shown in Fig. 2(a).
The CT and AW phases coexist in the sample with the patterns of the two phases overlapping. No significant changes in the patterns could be observed at the long range. However, the CT:AW4 and CT:AW8 samples exhibit additional peaks at 18.6° and 28.7°, which could be associated to the presence of CaWO₄ as the additional phase, according to the JCPDS card No. 41-1431 [36]. CaCO₃ is also present in the sample as evidenced by the peak observed at 29.5° that could be indexed according to JCPDS card No. 5-586. The amorphous phase is observed in higher amounts in the CT sample than that observed in the CT:AW16 and CT:AW32 samples, probably favoring the formation of the CaWO₄ and CaCO₃ phases. These phases serve as an interface between CT and AW, thereby changing the properties of the samples.

Short-range modifications can be observed from the Raman spectra of the samples (Fig. 2(b)). The CT:AW4 sample exhibits six Raman-active vibrational modes typical of the CaWO₄ crystal with two external vibration modes associated with CaO₆, observed at 81 cm⁻¹ corresponding to the bending mode (B_g) and at 153 cm⁻¹ corresponding to the stretching mode (E_g). Four modes associated with vibrations in the [WO₄] cluster are observed at 327, 388, 775, and 901 cm⁻¹, which correspond to the A_3 + B_3 bending mode, B_3 bending mode, E_g as-stretching mode, and A_1 stretching mode [37].

However, the Raman spectra of the CT:AW samples (8, 16, and 32 min) exhibit peaks corresponding to only CT and AW. A large change can be observed in the peaks observed for the decorated samples due to the structural order-disorder effects occurring at the interfacial region. The surface interaction between CT and AW in the decorated sample results in distortion in the short-range structural order in the [TiO₆] clusters. However, some of the vibrational modes of AW cannot be observed in the decorated samples, probably because the intensity of the CT modes is much higher than that of the AW vibrational modes.

Fig. 2(c) shows the FE-SEM images of the decorated samples. The images reveal the presence of hexagonal rod-shaped AW deposited on the surface of the CT cubes, resulting in the formation of the decorated samples (CT:AW). The contact area between the CT and AW particles in the CT:AW4 decorated sample is illustrated in the TEM images recorded with different magnifications (Fig. 3). Aggregated AW rod-like particles surrounding the CT cube are observed in the low-magnification image (Fig. 3(a)).

The junction between the CT and AW interface (Fig. 3(b)) indicates a strong interaction between the two materials, favoring the formation of CaWO₄ as observed from the XRD and Raman examination results.

3.1. UV–vis diffuse reflectance spectroscopy

The experimental optical band gap energy (E_{gap}) values for the CT samples synthesized with different times (4, 8, 16, and 32 min) at 140 °C are presented in Fig. 4. The E_{gap} for the samples were calculated using the Kubelka-Munk and Wood-Tauc equations [38,39].

The CT samples obtained using different synthesis times absorb photons in the wavelength range of 336–343 nm. An increase in the synthesis time does not cause a significant change in the E_{gap} values. However, the obtained E_{gap} values are lower than the corresponding theoretical values reported in the literature (3.98 eV) for the CT sample.
obtained by the MAH method \[18\]. The changes in the experimental and theoretical $E_{\text{gap}}$ values could be attributed to the presence of structural order-disorder in the material that depends on the synthesis time.

The experimental $E_{\text{gap}}$ value obtained for AW is 3.20 eV that corresponds to the absorption of photons in the wavelength of 387.5 nm (Fig. 5). The $E_{\text{gap}}$ value is less than the corresponding theoretically calculated (3.55 eV) value reported earlier \[8\]. The decrease in the $E_{\text{gap}}$ value could be attributed to the intermediate-range distortions in the sample caused by the presence of the structural and surface defects \[40\].

The $E_{\text{gap}}$ values of the decorated samples are shown in Fig. 6. The band gap values of CT:AW4, CT:AW8, CT:AW16, and CT:AW32 are 3.00, 3.09, 2.68, and 3.34 eV, respectively. The excitation spectra monitoring the maximum emission bands of the CT samples are presented in Fig. S3.

3.2. PL

Fig. 7 illustrates the PL spectra recorded with an excitation wavelength of 350 nm for the CT samples synthesized by the MAH method with different times. The excitation spectra monitoring the maximum emission bands of the CT samples are presented in Fig. S3.

All the CT samples exhibit a broadband profile corresponding to a multi-photon process. The 4, 16, and 32 min CT samples exhibit the maximum PL emission in the blue region, and the 8 min CT sample exhibits the maximum PL emission in the orange region (605 nm).

Using the Voigt Area G/L function, the PL curve of the CT samples was deconvoluted to four components at 445 nm (blue), 493 nm
(green), 567 nm (yellow), and 645 nm (red) (Fig. 7), corresponding to the electronic transition occurring at 2.79 eV, 2.51 eV, 2.19 eV, and 1.92 eV, respectively. The electronic transition values indicate that the PL emission occurs because of the participation of various electronic states within the band gap. These electronic states are formed as a result of the various relaxation processes [18] since the $E_{gap}$ experimental values of the CT samples are higher. There is a trapping electron favoring an emission in the blue region, corresponding to the shallow defects located near the conduction and valence bands for the 4, 16, and 32 min CT samples. These defects are caused by breaking of the symmetry processes in the $[TiO_x]$ and $[CaO_{12}]$ clusters [41].

The PL spectrum of the 8 min CT sample synthesized exhibits a new peak in the red region, which is associated with the deep levels within the band gap and is caused by O vacancies. By increasing the synthesis time, samples exhibiting different PL profiles are obtained, consequently achieving emissions in the blue, green, yellow, and red regions.

The PL curve of AW indicates a broadband profile, which is associated to the multi-photon process (Fig. 8) and the excitation spectra monitored by the maximum values of the emission (460, 595, 781 nm) were exhibited in Fig. S4. The PL curve was deconvoluted using the Voigt Area G/L function to four individual components at 450 nm (blue), 555 nm (green), 676 nm (red), and 783 nm (infrared). AW is known to be composed of $[WO_6]$ and $[AgO_x]$ ($x=2, 4, 6, 7$) clusters. The presence of shallow defects, the deformation in the Ag-O and W-O bonds, and the polarization in the lattice lead to the formation of $[WO_4]/[WO_6]^-$ or $[AgO_x]/[AgO_x]^-$ clusters. These distorted clusters cause the occurrence of more energetic emissions in the blue light region, as evidenced from the peaks observed at 450 and 555 nm. Defects such as Ag and O vacancies present in the $[AgO_x]$ and $[WO_6]$ clusters, classified as deep defects and less energetic, cause emissions in the red region, which can be associated to the peaks observed at 676 and 783 nm [21, 42, 43].

Fig. 9 shows the PL spectra of the CT:AW samples and Fig. S5 exhibited PL excitation spectra under maximum emission at 450 and 675 nm. A broadband is observed in the visible region with two maximum emissions centered at 450 nm (blue region) and 675 nm (red region). The emission in the blue region corresponds to the distortions present in the clusters of the two materials, and this emission is observed in pure CT and AW. Furthermore, the interaction between AW and CT causes short-range distortions in the $[TiO_x]$ clusters, due to an increase in the Ti-O bonding distance as well as the possible O vacancies present. The generated structural defects might cause the formation of various states in the band gap, which act as carrier recombination centers favoring the PL emission in the red region.

The deconvolution of the PL spectra of the decorated samples was carried out using the Voigt Area G/L function to obtain three peaks centered at 450 nm (blue), 559 nm (green), and 673 nm (red). Since Ca$^{2+}$ is a stronger base than Ag$^+$, the interaction between the...
The Ag and O vacancies network by forming Ag2O, resulting in the formation of [WO4] that network. In this process, two Ag atoms and one O atom leave the diagram. The colors of the decorated samples correspond to purplish pink to red (Fig. 10(a)-(d)). The chromaticity coordinates, x and y, of all the samples are given in Table 1.

In our model, the ideal photoluminescent crystal should exhibit some specific features. As noted in the previous analyses, our CT and AW crystals exhibit order–disorder structural defects ascribed to different types of distorted clusters [TiO6]d, [CaO12]d, ([WO6]d, [AgO4]d, [AgO6]d, and [AgO7]d) as well as ordered clusters [TiO6]o, [CaO12]o, ([WO6]o, [AgO4]o, [AgO6]o, and [AgO7]o). In addition, other characteristics, such as crystallographic preferred orientation, intermediary electronic levels, roughness, defects, and adsorption—desorption of decoration, are also important for properly analyzing the activity of different semiconductor crystals. Our CT and AW semiconductor samples exhibit the ability to generate electron and hole pairs. This characteristic can be attributed to the intrinsic defects present in the lattice of semiconductor materials having intermediary levels between the valence band and the conduction band, resulting in different PL properties and consequently different defect densities. Therefore, the presence of CT and AW in the crystals with different intermediate electronic levels, which consequently polarize the lattice, leads to different electronic transitions between ordered/distorted interfaces. The PL results show the variation AW defects in crystals, and CT as well as the influence caused at the interface. On the other hand, the study indicates that PL is a valuable tool for analyzing the interaction between semiconductors.

### Table 1

<table>
<thead>
<tr>
<th>Samples</th>
<th>x</th>
<th>y</th>
</tr>
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<tbody>
<tr>
<td>CT (4 min)</td>
<td>0.215</td>
<td>0.270</td>
</tr>
<tr>
<td>CT (8 min)</td>
<td>0.518</td>
<td>0.397</td>
</tr>
<tr>
<td>CT (16 min)</td>
<td>0.216</td>
<td>0.293</td>
</tr>
<tr>
<td>CT (32 min)</td>
<td>0.273</td>
<td>0.346</td>
</tr>
<tr>
<td>AW</td>
<td>0.405</td>
<td>0.311</td>
</tr>
<tr>
<td>CT:AW4</td>
<td>0.461</td>
<td>0.305</td>
</tr>
<tr>
<td>CT:AW8</td>
<td>0.573</td>
<td>0.318</td>
</tr>
<tr>
<td>CT:AW16</td>
<td>0.470</td>
<td>0.289</td>
</tr>
<tr>
<td>CT:AW32</td>
<td>0.420</td>
<td>0.299</td>
</tr>
</tbody>
</table>

AW clusters ([AgOx]/[WO6]) and the CT clusters ([CaO12]/[TiO6]) would result in the removal of Ag by Ca from the crystalline AW network. In this process, two Ag atoms and one O atom leave the network by forming Ag2O, resulting in the formation of [WO4] that interacts with Ca2+ in order to form CaWO4. The Ag and O vacancies are formed in the CT:AW samples (4 and 8 min) in which the bonding is not fully ordered in the long-range, thereby favoring the process. This is main responsible for the emission occurring in the red region 673 nm (1.84 eV).

The decorated CT:AW (4, 16, and 32 min) samples exhibit a strong emission in the blue region, at 450 nm (2.75 eV). However, the contact and sum of the both the emissions between the two semiconductor (CT and AW) favor a higher percentage of emission in the red region in the visible spectrum for all the decorated samples.

The CIE chromaticity diagram defining the colors of the samples is presented in Fig. 10. The pure CT samples exhibits a noticeable change in the color, which is influenced by varying the synthesis time that affects the distortion of [CaO12][TiO6] clusters. The CT samples exhibit colors prospects of blue, cyan, and orange (Fig. 10(e)-(h)).

The PL spectra profile of AW indicates a broadband that covers the blue and red regions. Hence, AW exhibits a purplish pink color, in agreement with the literature (Fig. 10(f)) [44].

The PL spectra of the CT:AW samples indicate that the interactions between the [AgO4]/[WO6]–[CaO12]/[TiO6] clusters favored emission in the red region, which can be observed from the chromaticity diagram. The colors of the decorated samples correspond to purplish pink to red (Fig. 10(a)-(d)). The chromaticity coordinates, x and y, of all the samples are given in Table 1.

### 4. Conclusions

In summary, we have discussed the PL properties of the AW decorated CT samples prepared in this study. PL is favored in materials exhibiting structural disorders in the short, medium, and long ranges. The use of the MAH method resulted in the formation of CT samples with structural disorders. All the CT samples exhibited emission at room temperature owing to the presence of intermediate energy levels within the band gap since the emission wavelength was smaller than the experimentally obtained Eg values. The PL spectra of CT samples showed an enhanced in the red emission part due the decorating with AW (CT:AW), since, an emission that covering the entire visible spectrum, with two maximum emissions (blue and red region), was achieved. This phenomenon is justified by interface effects inducing short-range defects in the [TiO4] clusters. The CIE chromaticity diagram indicates a favorable red-light emission for the samples.

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### Appendix A. Supporting information

Supplementary data associated with this article can be found in the online version at http://dx.doi.org/10.1016/j.ceramint.2017.01.121.

### References


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